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# STEPPER MOTOR CONTROLLER IC

Check for Samples: DRV8825

## FEATURES

- PWM Microstepping Motor Driver
  - Built-In Microstepping Indexer
  - Five-Bit Winding Current Control Allows Up to 32 Current Levels
  - Low MOSFET On-Resistance
- 2.5-A Maximum Drive Current at 24 V, 25°C
- **Built-In 3.3-V Reference Output**
- 8.2-V to 45-V Operating Supply Voltage Range
- **Thermally Enhanced Surface Mount Package**

### APPLICATIONS

- **Automatic Teller Machines**
- **Money Handling Machines**
- **Video Security Cameras**
- **Printers**
- Scanners
- **Office Automation Machines**
- **Gaming Machines**
- **Factory Automation**
- Robotics

### DESCRIPTION

The DRV8825 provides an integrated motor driver solution for printers, scanners, and other automated equipment applications. The device has two H-bridge drivers, and can drive a bipolar stepper motor or two DC motors. The output driver block for each consists of N-channel power MOSFET's configured as full H-bridges to drive the motor windings. The DRV8825 can supply up to 2.5-A peak or 1.75-A RMS output current (with proper heatsinking at 24 V and 25°C).

A simple step/direction interface allows easy interfacing to controller circuits. Pins allow configuration of the motor in full-step up to 1/32-step modes. Decay mode is programmable.

Internal shutdown functions are provided for overcurrent protection, short circuit protection, undervoltage lockout and overtemperature.

The DRV8825 is available in a 28-pin HTSSOP package with PowerPAD™ (Eco-friendly: RoHS & no Sb/Br).

### ORDERING INFORMATION<sup>(1)</sup>

PACKAGE <sup>(2)</sup>			TOP-SIDE MARKING
PowerPAD™ (HTSSOP) - PWP	Reel of 2000	DRV8825PWPR	8825

For the most current packaging and ordering information, see the Package Option Addendum at the end of this document, or see the TI (1) web site at www.ti.com.

(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.



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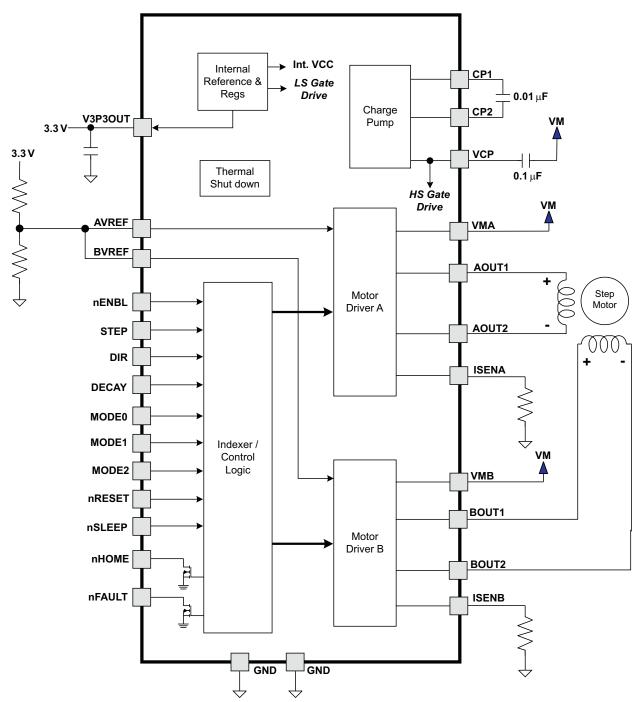
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DEVICE INFORMATION

Functional Block Diagram



TEXAS INSTRUMENTS

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### Table 1. TERMINAL FUNCTIONS

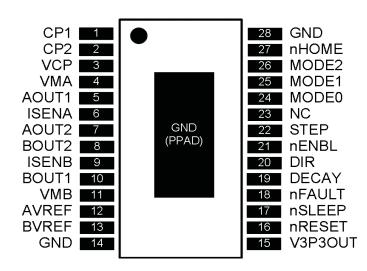
NAME PIN I/O <sup>(1)</sup>		ME PIN I/O <sup>(1)</sup> DESCRIPTION		EXTERNAL COMPONENTS OR CONNECTIONS
POWER AND	GROUND			
GND	14, 28	-	Device ground	
VMA	4	-	Bridge A power supply	Connect to motor supply (8.2 - 45 V). Both
VMB	11	-	Bridge B power supply	pins must be connected to same supply.
V3P3OUT	15	0	3.3-V regulator output	Bypass to GND with a 0.47-µF 6.3-V ceramic capacitor. Can be used to supply VREF.
CP1	1	IO	Charge pump flying capacitor	Connect a 0.01-µF 50-V capacitor between
CP2	2	10	Charge pump flying capacitor	CP1 and CP2.
VCP	3	ю	High-side gate drive voltage	Connect a 0.1- $\mu$ F 16-V ceramic capacitor to VM.
CONTROL				· ·
nENBL	21	I	Enable input	Logic high to disable device outputs and indexer operation, logic low to enable. Internal pulldown.
nSLEEP	17	I	Sleep mode input	Logic high to enable device, logic low to enter low-power sleep mode. Internal pulldown.
STEP	22	I	Step input	Rising edge causes the indexer to move one step. Internal pulldown.
DIR	20	I	Direction input	Level sets the direction of stepping. Internal pulldown.
MODE0	24	I	Microstep mode 0	MODE0 - MODE2 set the step mode - full,
MODE1	25	I	Microstep mode 1	1/2, 1/4, 1/8/ 1/16, or 1/32 step. Internal
MODE2	26	I	Microstep mode 2	pulldown.
DECAY	19	I	Decay mode	Low = slow decay, open = mixed decay, high = fast decay. Internal pulldown and pullup.
nRESET	16	I	Reset input	Active-low reset input initializes the indexer logic and disables the H-bridge outputs. Internal pulldown.
AVREF	12	I	Bridge A current set reference input	Reference voltage for winding current set.
BVREF	13	I	Bridge B current set reference input	Normally AVREF and BVREF are connected to the same voltage. Can be connected to V3P3OUT.
STATUS				· ·
nHOME	27	OD	Home position	Logic low when at home state of step table
nFAULT	18	OD	Fault	Logic low when in fault condition (overtemp, overcurrent)
OUTPUT				
ISENA	6	IO	Bridge A ground / Isense	Connect to current sense resistor for bridge A.
ISENB	9	IO	Bridge B ground / Isense	Connect to current sense resistor for bridge B.
AOUT1	5	0	Bridge A output 1	Connect to bipolar stepper motor winding A.
AOUT2	7	0	Bridge A output 2	Positive current is AOUT1 $\rightarrow$ AOUT2
BOUT1	10	0	Bridge B output 1	Connect to bipolar stepper motor winding B.
BOUT2	8	0	Bridge B output 2	Positive current is BOUT1 $\rightarrow$ BOUT2

(1) Directions: I = input, O = output, OZ = tri-state output, OD = open-drain output, IO = input/output

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## ABSOLUTE MAXIMUM RATINGS<sup>(1)(2)</sup>

			VALUE	UNIT
VMx	Power supply voltage range		-0.3 to 47	V
	Digital pin voltage range		–0.5 to 7	V
VREF	Input voltage	–0.3 to 4	V	
	ISENSEx pin voltage		-0.3 to 0.8	V
	Peak motor drive output current, t < 1 µS	Internally limited	А	
	Continuous motor drive output current <sup>(3)</sup>	2.5	А	
		HBD (human body model)	2000	
	ESD rating	CDM (charged device model)	500	V
	Continuous total power dissipation	See Dissipation Rating	gs table	
TJ	Operating junction temperature range		-40 to 150	°C
T <sub>stg</sub>	Storage temperature range		-60 to 150	°C

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to network ground terminal.

(3) Power dissipation and thermal limits must be observed.

### THERMAL INFORMATION

		DRV8825	
	THERMAL METRIC <sup>(1)</sup>	PWP	UNITS
		28 PINS	
θ <sub>JA</sub>	Junction-to-ambient thermal resistance <sup>(2)</sup>	31.6	
θ <sub>JCtop</sub>	Junction-to-case (top) thermal resistance <sup>(3)</sup>	15.9	
$\theta_{JB}$	Junction-to-board thermal resistance <sup>(4)</sup>	5.6	°C 444
ΨJT	Junction-to-top characterization parameter <sup>(5)</sup>	0.2	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter <sup>(6)</sup>	5.5	
θ <sub>JCbot</sub>	Junction-to-case (bottom) thermal resistance <sup>(7)</sup>	1.4	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.

(2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.

(3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

(4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.

(5) The junction-to-top characterization parameter,  $\psi_{JT}$ , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining  $\theta_{JA}$ , using a procedure described in JESD51-2a (sections 6 and 7).

(6) The junction-to-board characterization parameter,  $\psi_{JB}$ , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining  $\theta_{JA}$ , using a procedure described in JESD51-2a (sections 6 and 7).

(7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

### **RECOMMENDED OPERATING CONDITIONS**

		MIN	NOM MAX	UNIT
V <sub>M</sub>	Motor power supply voltage range <sup>(1)</sup>	8.2	45	V
V <sub>REF</sub>	VREF input voltage <sup>(2)</sup>	1	3.5	V
I <sub>V3P3</sub>	V3P3OUT load current	0	1	mA

(1) All  $V_{\text{M}}$  pins must be connected to the same supply voltage.

(2) Operational at VREF between 0 V and 1 V, but accuracy is degraded.

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STRUMENTS

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### **ELECTRICAL CHARACTERISTICS**

over operating free-air temperature range of -40°C to 85°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER	SUPPLIES					
VМ	VM operating supply current	$V_{M} = 24 V$		5	8	mA
I <sub>VMQ</sub>	VM sleep mode supply current	V <sub>M</sub> = 24 V		10	20	μA
V <sub>UVLO</sub>	VM undervoltage lockout voltage	V <sub>M</sub> rising		7.8	8.2	V
V3P3OU	JT REGULATOR	· · · · · ·				
V <sub>3P3</sub>	V3P3OUT voltage	IOUT = 0 to 1 mA	3.2	3.3	3.4	V
LOGIC-I	LEVEL INPUTS	•				
V <sub>IL</sub>	Input low voltage			0.6	0.7	V
VIH	Input high voltage		2.2		5.25	V
V <sub>HYS</sub>	Input hysteresis		0.3	0.45	0.6	V
IIL	Input low current	VIN = 0	-20		20	μA
IIH	Input high current	VIN = 3.3 V			100	μA
R <sub>PD</sub>	Internal pulldown resistance			100		kΩ
nHOME,	, nFAULT OUTPUTS (OPEN-DRAI	N OUTPUTS)			,	
V <sub>OL</sub>	Output low voltage	I <sub>O</sub> = 5 mA			0.5	V
I <sub>OH</sub>	Output high leakage current	V <sub>O</sub> = 3.3 V			1	μA
DECAY	INPUT	· · · · · · · · · · · · · · · · · · ·				
V <sub>IL</sub>	Input low threshold voltage	For slow decay mode			0.8	V
V <sub>IH</sub>	Input high threshold voltage	For fast decay mode	2			V
I <sub>IN</sub>	Input current				±40	μA
R <sub>PU</sub>	Internal pullup resistance (up to 3.3 V)			130		kΩ
R <sub>PD</sub>	Internal pulldown resistance			80		kΩ
H-BRID	GE FETS	· · · · · ·				
		V <sub>M</sub> = 24 V, I <sub>O</sub> = 1 A, T <sub>J</sub> = 25°C		0.2		
-	HS FET on resistance	V <sub>M</sub> = 24 V, I <sub>O</sub> = 1 A, T <sub>J</sub> = 85°C		0.25	0.32	
R <sub>DS(ON)</sub>		V <sub>M</sub> = 24 V, I <sub>O</sub> = 1 A, T <sub>J</sub> = 25°C		0.2		Ω
	LS FET on resistance	V <sub>M</sub> = 24 V, I <sub>O</sub> = 1 A, T <sub>J</sub> = 85°C		0.25	0.32	
I <sub>OFF</sub>	Off-state leakage current		-20		20	μA
MOTOR	DRIVER	· · · · · ·				
f	Internal current control PWM			30		kHz
f <sub>PWM</sub>	frequency			50		κι iΖ
t <sub>BLANK</sub>	Current sense blanking time			4		μs
t <sub>R</sub>	Rise time		30		200	ns
t <sub>F</sub>	Fall time		30		200	ns
	CTION CIRCUITS					
I <sub>OCP</sub>	Overcurrent protection trip level		3			Α
t <sub>OCP</sub>	Overcurrent protection deglitch time			2.5		μs
t <sub>TSD</sub>	Thermal shutdown temperature	Die temperature	150	160	180	°C
CURREI	NT CONTROL	1				
I <sub>REF</sub>	xVREF input current	xVREF = 3.3 V	-3		3	μA
V <sub>TRIP</sub>	xISENSE trip voltage	xVREF = 3.3 V, 100% current setting	635	660	685	mV
		xVREF = 3.3 V, 5% current setting	-25		25	
A 1	Current trip accuracy	xVREF = 3.3 V, 10%-34% current setting	-15		15	07
∆I <sub>TRIP</sub>	(relative to programmed value)	xVREF = 3.3 V, 38%-67% current setting	-10		10	%
		xVREF = 3.3 V, 71%-100% current setting	-5		5	



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# ELECTRICAL CHARACTERISTICS (continued)

over operating free-air temperature range of -40°C to 85°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
A <sub>ISENSE</sub>	Current sense amplifier gain	Reference only		5		V/V

### TIMING REQUIREMENTS

			MIN	MAX	UNIT
1	f <sub>STEP</sub>	Step frequency		250	kHz
2	t <sub>WH(STEP)</sub>	Pulse duration, STEP high	1.9		μs
3	t <sub>WL(STEP)</sub>	Pulse duration, STEP low	1.9		μs
4	t <sub>SU(STEP)</sub>	Setup time, command to STEP rising	650		ns
5	t <sub>H(STEP)</sub>	Hold time, command to STEP rising	650		ns
6	t <sub>ENBL</sub>	Enable time, nENBL active to STEP	650		ns
7	t <sub>WAKE</sub>	Wakeup time, nSLEEP inactive to STEP	1.7		ms

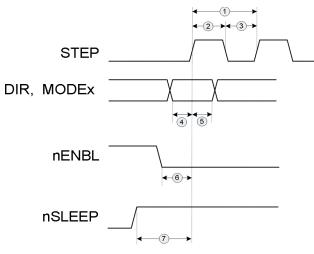


Figure 1. Timing Diagram

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## FUNCTIONAL DESCRIPTION

### **PWM Motor Drivers**

The DRV8825 contains two H-bridge motor drivers with current-control PWM circuitry. A block diagram of the motor control circuitry is shown in Figure 2.

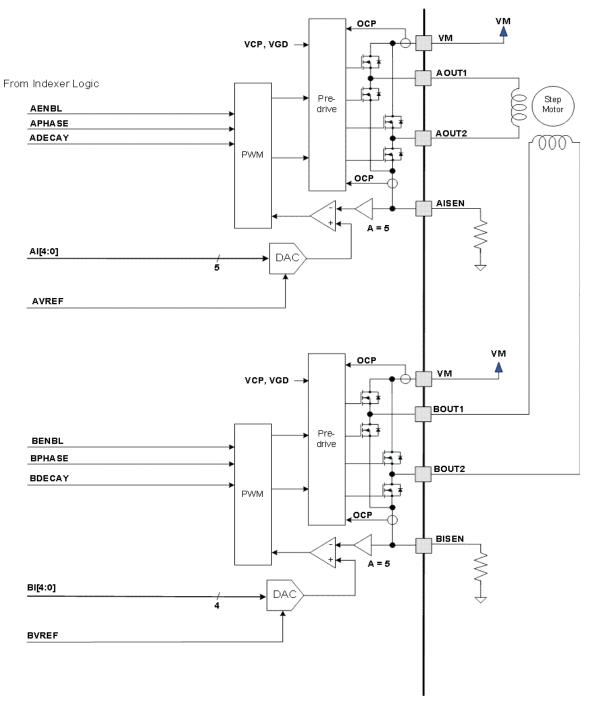


Figure 2. Motor Control Circuitry

Note that there are multiple VM motor power supply pins. All VM pins must be connected together to the motor supply voltage.



#### **Current Regulation**

The current through the motor windings is regulated by a fixed-frequency PWM current regulation, or current chopping. When an H-bridge is enabled, current rises through the winding at a rate dependent on the DC voltage and inductance of the winding. Once the current hits the current chopping threshold, the bridge disables the current until the beginning of the next PWM cycle.

In stepping motors, current regulation is used to vary the current in the two windings in a semi-sinusoidal fashion to provide smooth motion.

The PWM chopping current is set by a comparator which compares the voltage across a current sense resistor connected to the xISEN pins, multiplied by a factor of 5, with a reference voltage. The reference voltage is input from the xVREF pins.

The full-scale (100%) chopping current is calculated in Equation 1.

$$I_{CHOP} = \frac{V_{REFX}}{5 \cdot R_{ISENSE}}$$

(1)

Example:

If a 0.25- $\Omega$  sense resistor is used and the VREFx pin is 2.5 V, the full-scale (100%) chopping current will be 2.5 V / (5 x 0.25  $\Omega$ ) = 2 A.

The reference voltage is scaled by an internal DAC that allows fractional stepping of a bipolar stepper motor, as described in the microstepping indexer section below.

### Decay Mode

During PWM current chopping, the H-bridge is enabled to drive current through the motor winding until the PWM current chopping threshold is reached. This is shown in Figure 3 as case 1. The current flow direction shown indicates positive current flow.

Once the chopping current threshold is reached, the H-bridge can operate in two different states, fast decay or slow decay.

In fast decay mode, once the PWM chopping current level has been reached, the H-bridge reverses state to allow winding current to flow in a reverse direction. As the winding current approaches zero, the bridge is disabled to prevent any reverse current flow. Fast decay mode is shown in Figure 3 as case 2.

In slow decay mode, winding current is re-circulated by enabling both of the low-side FETs in the bridge. This is shown in Figure 3 as case 3.

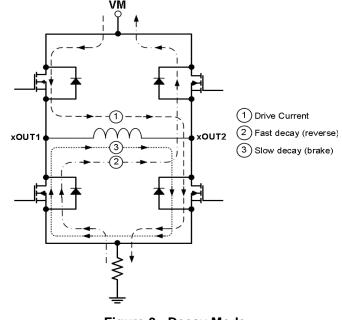


Figure 3. Decay Mode

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The DRV8825 supports fast decay, slow decay and a mixed decay mode. Slow, fast, or mixed decay mode is selected by the state of the DECAY pin - logic low selects slow decay, open selects mixed decay operation, and logic high sets fast decay mode. The DECAY pin has both an internal pullup resistor of approximately 130 k $\Omega$  and an internal pulldown resistor of approximately 80 k $\Omega$ . This sets the mixed decay mode if the pin is left open or undriven.

Mixed decay mode begins as fast decay, but at a fixed period of time (75% of the PWM cycle) switches to slow decay mode for the remainder of the fixed PWM period. This occurs only if the current through the winding is decreasing (per the indexer step table); if the current is increasing, then slow decay is used.

### Blanking Time

After the current is enabled in an H-bridge, the voltage on the xISEN pin is ignored for a fixed period of time before enabling the current sense circuitry. This blanking time is fixed at  $3.75 \ \mu$ s. Note that the blanking time also sets the minimum on time of the PWM.

### **Microstepping Indexer**

Built-in indexer logic in the DRV8825 allows a number of different stepping configurations. The MODE0 - MODE2 pins are used to configure the stepping format as shown in Table 2.

MODE2	MODE1	MODE0	STEP MODE	
0	0	0	Full step (2-phase excitation) with 71% current	
0	0	1	1/2 step (1-2 phase excitation)	
0	1	0	1/4 step (W1-2 phase excitation)	
0	1	1	8 microsteps / step	
1	0	0	16 microsteps / step	
1	0	1	32 microsteps / step	
1	1	0	32 microsteps / step	
1	1	1	32 microsteps / step	

#### Table 2. Stepping Format

Table 3 shows the relative current and step directions for different settings of MODEx. At each rising edge of the STEP input, the indexer travels to the next state in the table. The direction is shown with the DIR pin high; if the DIR pin is low the sequence is reversed. Positive current is defined as xOUT1 = positive with respect to xOUT2.

Note that if the step mode is changed while stepping, the indexer will advance to the next valid state for the new MODEx setting at the rising edge of STEP.

The home state is 45°. This state is entered at power-up or application of nRESET. This is shown in Table 3 by the shaded cells. The logic inputs DIR, STEP, nRESET and MODEx have internal pulldown resistors of 100 k $\Omega$ .

1/32 STEP	1/16 STEP	1/8 STEP	1/4 STEP	1/2 STEP	FULL STEP 70%	WINDING CURRENT A	WINDING CURRENT B	ELECTRICAL ANGLE
1	1	1	1	1		100%	0%	0
2						100%	5%	3
3	2					100%	10%	6
4						99%	15%	8
5	3	2				98%	20%	11
6						97%	24%	14
7	4					96%	29%	17
8						94%	34%	20
9	5	3	2			92%	38%	23
10						90%	43%	25
11	6					88%	47%	28

**Table 3. Relative Current and Step Directions** 



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1/32 STEP	1/16 STEP	1/8 STEP	1/4 STEP	1/2 STEP	FULL STEP 70%	WINDING CURRENT A	WINDING CURRENT B	ELECTRICAL ANGLE
12						86%	51%	31
13	7	4				83%	56%	34
14						80%	60%	37
15	8					77%	63%	39
16						74%	67%	42
17	9	5	3	2	1	71%	71%	45
18						67%	74%	48
19	10					63%	77%	51
20						60%	80%	53
21	11	6				56%	83%	56
22		•				51%	86%	59
23	12					47%	88%	62
23	12					43%	90%	65
24	13	7	4			38%	90%	68
25	13	1	4			34%	92%	70
26	1.1							
	14					29%	96%	73
28	45	-				24%	97%	76
29	15	8				20%	98%	79
30	10					15%	99%	82
31	16					10%	100%	84
32						5%	100%	87
33	17	9	5	3		0%	100%	90
34						-5%	100%	93
35	18					-10%	100%	96
36						-15%	99%	98
37	19	10				-20%	98%	101
38						-24%	97%	104
39	20					-29%	96%	107
40						-34%	94%	110
41	21	11	6			-38%	92%	113
42						-43%	90%	115
43	22					-47%	88%	118
44						-51%	86%	121
45	23	12				-56%	83%	124
46						-60%	80%	127
47	24					-63%	77%	129
48						-67%	74%	132
49	25	13	7	4	2	-71%	71%	135
50						-74%	67%	138
51	26					-77%	63%	141
52						-80%	60%	143
53	27	14				-83%	56%	146
54						-86%	51%	149
55	28					-88%	47%	143
56						-90%	43%	155
57	29	15	8			-92%	38%	158

## Table 3. Relative Current and Step Directions (continued)

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Table 3. Relative Current and Step Directions (continued)								
1/32 STEP	1/16 STEP	1/8 STEP	1/4 STEP	1/2 STEP	FULL STEP 70%	WINDING CURRENT A	WINDING CURRENT B	ELECTRICAL ANGLE
58						-94%	34%	160
59	30					-96%	29%	163
60						-97%	24%	166
61	31	16				-98%	20%	169
62						-99%	15%	172
63	32					-100%	10%	174
64						-100%	5%	177
65	33	17	9	5		-100%	0%	180
66						-100%	-5%	183
67	34					-100%	-10%	186
68						-99%	-15%	188
69	35	18				-98%	-20%	191
70						-97%	-24%	194
71	36					-96%	-29%	197
72						-94%	-34%	200
73	37	19	10			-92%	-38%	203
74						-90%	-43%	205
75	38					-88%	-47%	208
76	00					-86%	-51%	211
77	39	20				-83%	-56%	214
78	00	20				-80%	-60%	217
79	40					-77%	-63%	219
80	-10					-74%	-67%	213
81	41	21	11	6	3	-71%	-71%	225
82	71	21		0	5	-67%	-74%	228
83	42					-63%	-74%	231
84	42					-60%	-80%	233
85	43	22				-56%	-83%	235
86	43	22				-51%	-86%	230
87	44					-47%	-88%	239
88	44					-47%	-00%	242
89	45	23	12			-38%	_90% _92%	243
	40	23	12					
90	40					-34%	-94%	250
91	46					-29%	-96%	253
92	47	0.4		<u> </u>		-24%	-97%	256
93	47	24		-		-20%	-98%	259
94	40			<u> </u>		-15%	-99%	262
95	48			-		-10%	-100%	264
96	10		4.5	_		-5%	-100%	267
97	49	25	13	7		0%	-100%	270
98						5%	-100%	273
99	50					10%	-100%	276
100						15%	-99%	278
101	51	26		-		20%	-98%	281
102						24%	-97%	284
103	52					29%	-96%	287

### Table 3. Relative Current and Step Directions (continued)

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1/32 STEP	1/16 STEP	1/8 STEP	1/4 STEP	1/2 STEP	FULL STEP 70%	WINDING CURRENT A	WINDING CURRENT B	ELECTRICAL ANGLE
104						34%	-94%	290
105	53	27	14			38%	-92%	293
106						43%	-90%	295
107	54					47%	-88%	298
108						51%	-86%	301
109	55	28				56%	-83%	304
110						60%	-80%	307
111	56					63%	-77%	309
112						67%	-74%	312
113	57	29	15	8	4	71%	-71%	315
114						74%	-67%	318
115	58					77%	-63%	321
116						80%	-60%	323
117	59	30				83%	-56%	326
118						86%	-51%	329
119	60					88%	-47%	332
120						90%	-43%	335
121	61	31	16			92%	-38%	338
122						94%	-34%	340
123	62					96%	-29%	343
124						97%	-24%	346
125	63	32				98%	-20%	349
126						99%	-15%	352
127	64					100%	-10%	354
128						100%	-5%	357

#### Table 3. Relative Current and Step Directions (continued)

### nRESET, nENBLE and nSLEEP Operation

The nRESET pin, when driven active low, resets internal logic, and resets the step table to the home position. It also disables the H-bridge drivers. The STEP input is ignored while nRESET is active.

The nENBL pin is used to control the output drivers and enable/disable operation of the indexer. When nENBL is low, the output H-bridges are enabled, and rising edges on the STEP pin are recognized. When nENBL is high, the H-bridges are disabled, the outputs are in a high-impedance state, and the STEP input is ignored.

Driving nSLEEP low will put the device into a low power sleep state. In this state, the H-bridges are disabled, the gate drive charge pump is stopped, the V3P3OUT regulator is disabled, and all internal clocks are stopped. In this state all inputs are ignored until nSLEEP returns inactive high. When returning from sleep mode, some time (approximately 1 ms) needs to pass before applying a STEP input, to allow the internal circuitry to stabilize. Note that nRESET and nENABLE have internal pulldown resistors of approximately 100 k $\Omega$ . The nSLEEP pin has an internal pulldown resistor of 1 M $\Omega$ . nSLEEP and nRESET signals need to be driven to logic high for device operation.

## **Protection Circuits**

The DRV8825 is fully protected against undervoltage, overcurrent and overtemperature events.

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#### **Overcurrent Protection (OCP)**

An analog current limit circuit on each FET limits the current through the FET by removing the gate drive. If this analog current limit persists for longer than the OCP time, all FETs in the H-bridge will be disabled and the nFAULT pin will be driven low. The device will remain disabled until either nRESET pin is applied, or VM is removed and re-applied.

Overcurrent conditions on both high and low side devices; i.e., a short to ground, supply, or across the motor winding will all result in an overcurrent shutdown. Note that overcurrent protection does not use the current sense circuitry used for PWM current control, and is independent of the I<sub>SENSE</sub> resistor value or VREF voltage.

#### Thermal Shutdown (TSD)

If the die temperature exceeds safe limits, all FETs in the H-bridge will be disabled and the nFAULT pin will be driven low. Once the die temperature has fallen to a safe level operation will automatically resume.

#### Undervoltage Lockout (UVLO)

If at any time the voltage on the VM pins falls below the undervoltage lockout threshold voltage, all circuitry in the device will be disabled and internal logic will be reset. Operation will resume when  $V_M$  rises above the UVLO threshold.



### THERMAL INFORMATION

#### Thermal Protection

The DRV8825 has thermal shutdown (TSD) as described above. If the die temperature exceeds approximately 150°C, the device will be disabled until the temperature drops to a safe level.

Any tendency of the device to enter TSD is an indication of either excessive power dissipation, insufficient heatsinking, or too high an ambient temperature.

### **Power Dissipation**

Power dissipation in the DRV8825 is dominated by the power dissipated in the output FET resistance, or  $R_{DS(ON)}$ . Average power dissipation when running a stepper motor can be roughly estimated by Equation 2.

$$P_{TOT} = 4 \cdot R_{DS(ON)} \cdot (I_{OUT(RMS)})^2$$

(2)

where  $P_{TOT}$  is the total power dissipation,  $R_{DS(ON)}$  is the resistance of each FET, and  $I_{OUT(RMS)}$  is the RMS output current being applied to each winding.  $I_{OUT(RMS)}$  is equal to the approximately 0.7x the full-scale output current setting. The factor of 4 comes from the fact that there are two motor windings, and at any instant two FETs are conducting winding current for each winding (one high-side and one low-side).

The maximum amount of power that can be dissipated in the device is dependent on ambient temperature and heatsinking.

Note that  $R_{DS(ON)}$  increases with temperature, so as the device heats, the power dissipation increases. This must be taken into consideration when sizing the heatsink.

### Heatsinking

The PowerPAD<sup>™</sup> package uses an exposed pad to remove heat from the device. For proper operation, this pad must be thermally connected to copper on the PCB to dissipate heat. On a multi-layer PCB with a ground plane, this can be accomplished by adding a number of vias to connect the thermal pad to the ground plane. On PCBs without internal planes, copper area can be added on either side of the PCB to dissipate heat. If the copper area is on the opposite side of the PCB from the device, thermal vias are used to transfer the heat between top and bottom layers.

For details about how to design the PCB, refer to TI application report SLMA002, " PowerPAD™ Thermally Enhanced Package" and TI application brief SLMA004, " PowerPAD™ Made Easy", available at www.ti.com.

In general, the more copper area that can be provided, the more power can be dissipated. It can be seen that the heatsink effectiveness increases rapidly to about 20 cm<sup>2</sup>, then levels off somewhat for larger areas.



### PACKAGING INFORMATION

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/ Ball Finish	MSL Peak Temp <sup>(3)</sup>	Samples (Requires Login)
DRV8825PWP	ACTIVE	HTSSOP	PWP	28	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	
DRV8825PWPR	ACTIVE	HTSSOP	PWP	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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# PACKAGE MATERIALS INFORMATION

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### TAPE AND REEL INFORMATION

#### REEL DIMENSIONS

TEXAS INSTRUMENTS





TAPE AND REEL INFORMATION

#### TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DRV8825PWPR	HTSSOP	PWP	28	2000	330.0	16.4	6.9	10.2	1.8	12.0	16.0	Q1

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# PACKAGE MATERIALS INFORMATION

14-Jul-2012



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DRV8825PWPR	HTSSOP	PWP	28	2000	367.0	367.0	38.0

PWP (R-PDSO-G28)

PowerPAD<sup>™</sup> PLASTIC SMALL OUTLINE

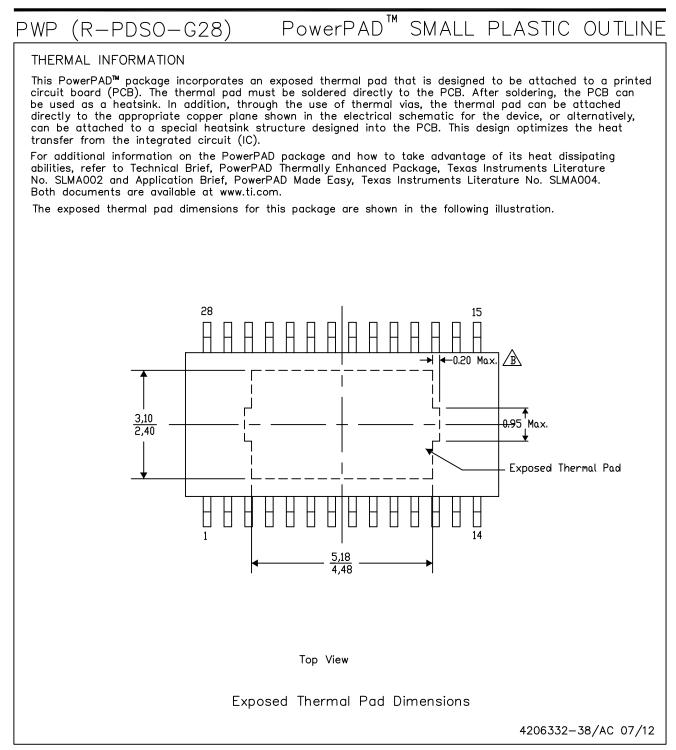


All linear dimensions are in millimeters. NOTES: Α.

- Β. This drawing is subject to change without notice.
- Body dimensions do not include mold flash or protrusions. Mold flash and protrusion shall not exceed 0.15 per side. C.
- This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad D.
- Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <a href="http://www.ti.com">http://www.ti.com</a>. E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions. E. Falls within JEDEC MO-153

PowerPAD is a trademark of Texas Instruments.

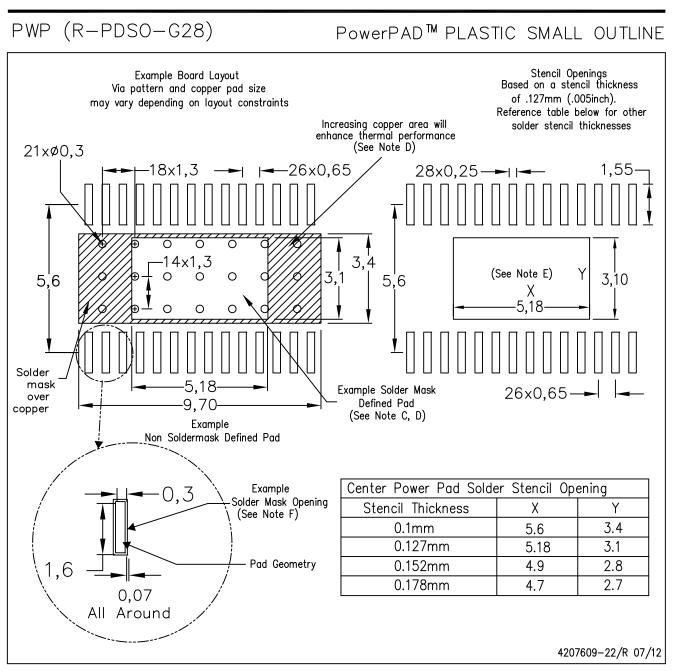




NOTE: A. All linear dimensions are in millimeters <u>A</u> Exposed tie strap features may not be present.

PowerPAD is a trademark of Texas Instruments





NOTES:

A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets.
- E. For specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <htp://www.ti.com>. Publication IPC-7351 is recommended for alternate designs. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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